

Supplementary Material

Crystalline Quality and Surface Morphology Improvement of Face-to-Face Annealed MBE-Grown AlN on h-BN

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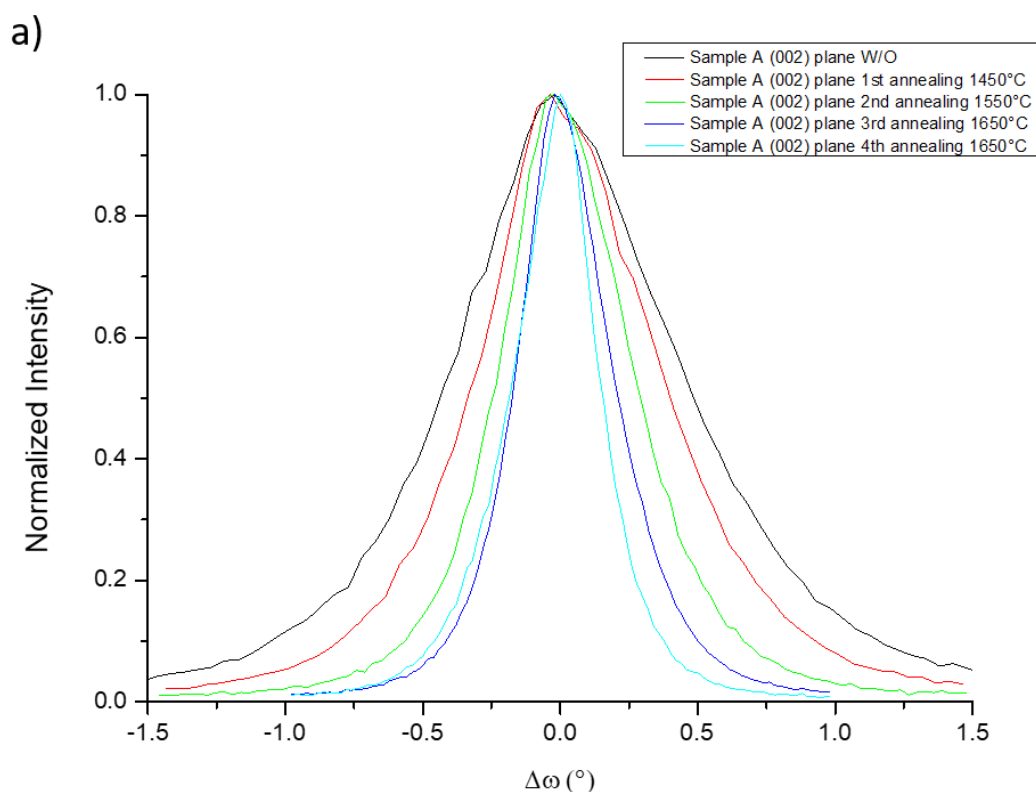
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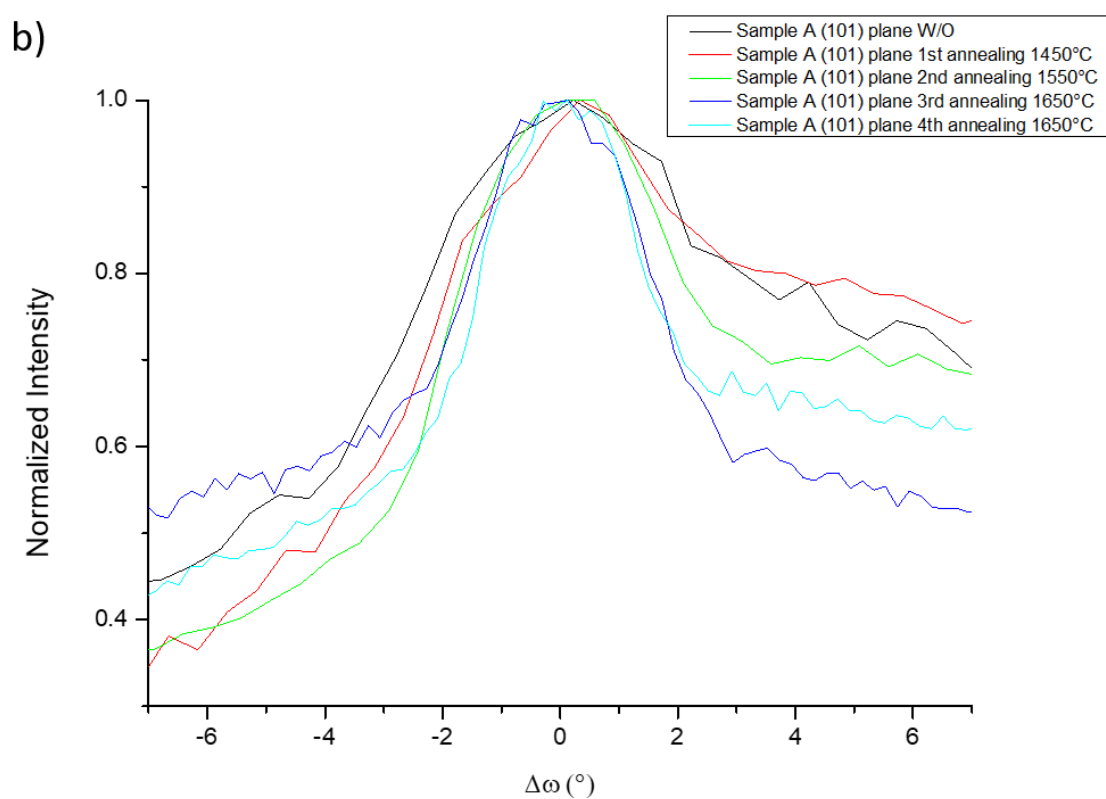


Figure S1. ω -scan of AlN (sample A) before and after FFA: (a) for the symmetric plane (0 0 0 2), (b) for the skew symmetric plane (1 0 -1 1).

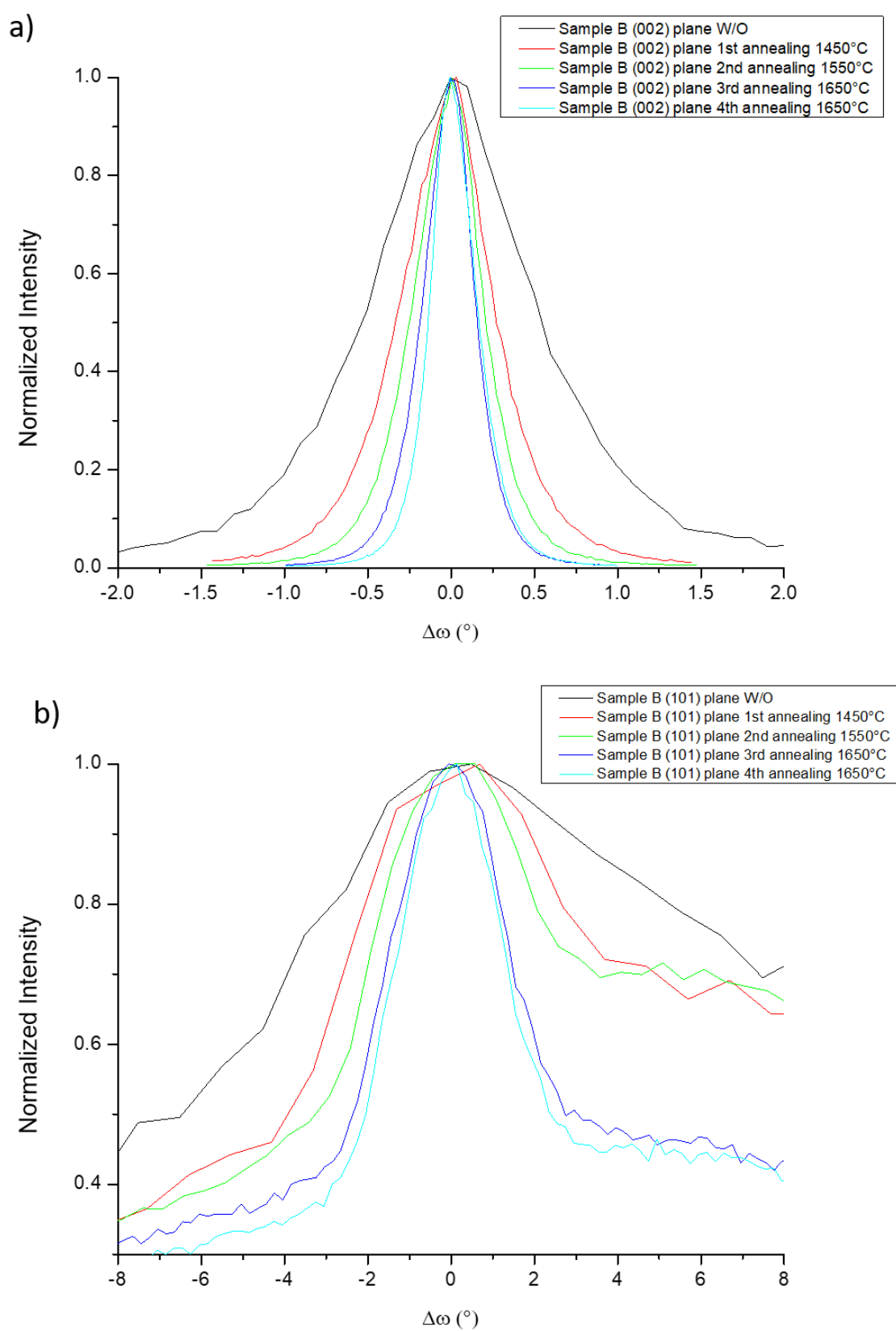
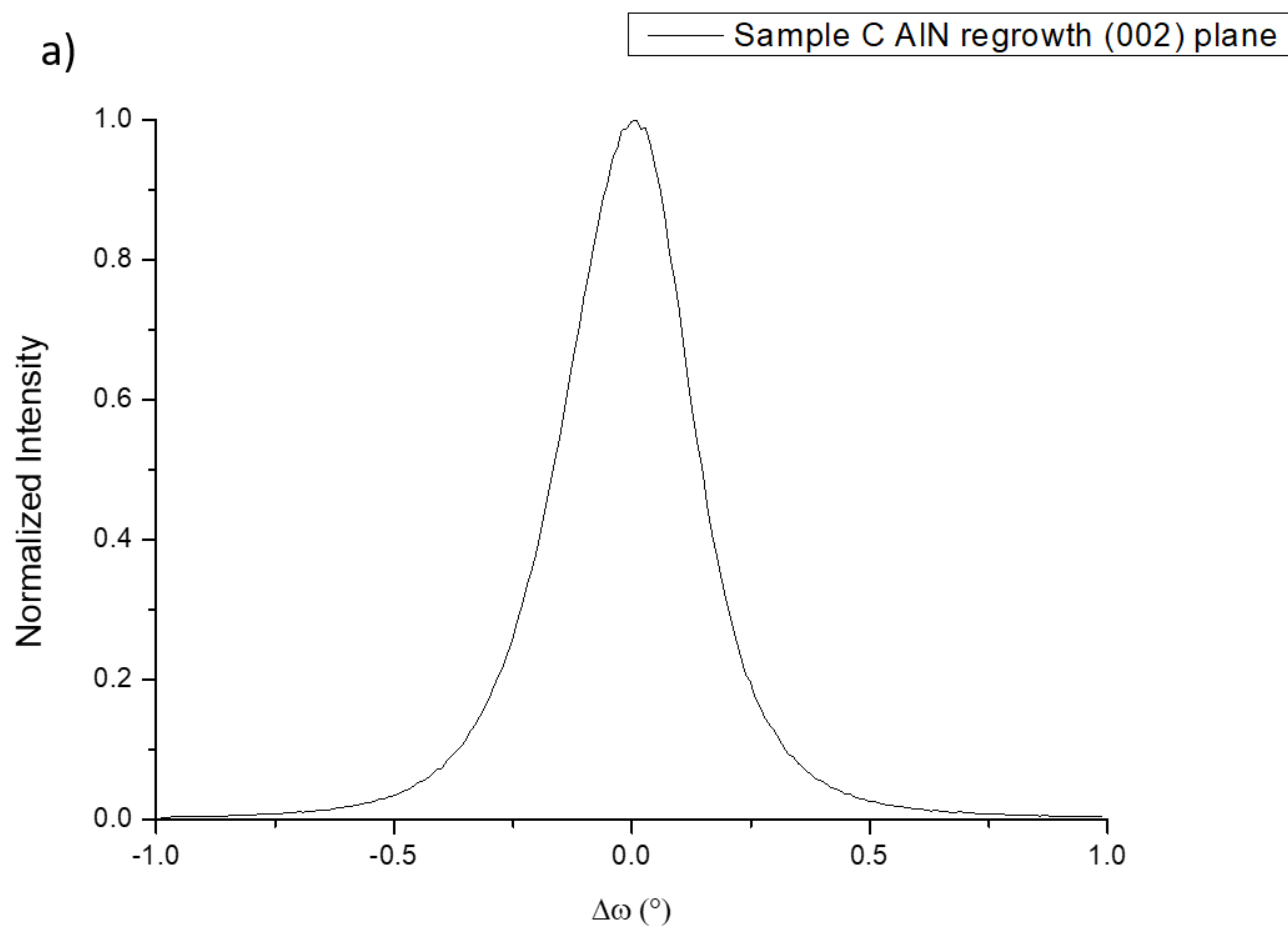


Figure S2. ω -scan of AlN (sample B) before and after FFA: (a) for the symmetric plane (0 0 0 2), (b) for the skew symmetric plane (1 0 -1 1).



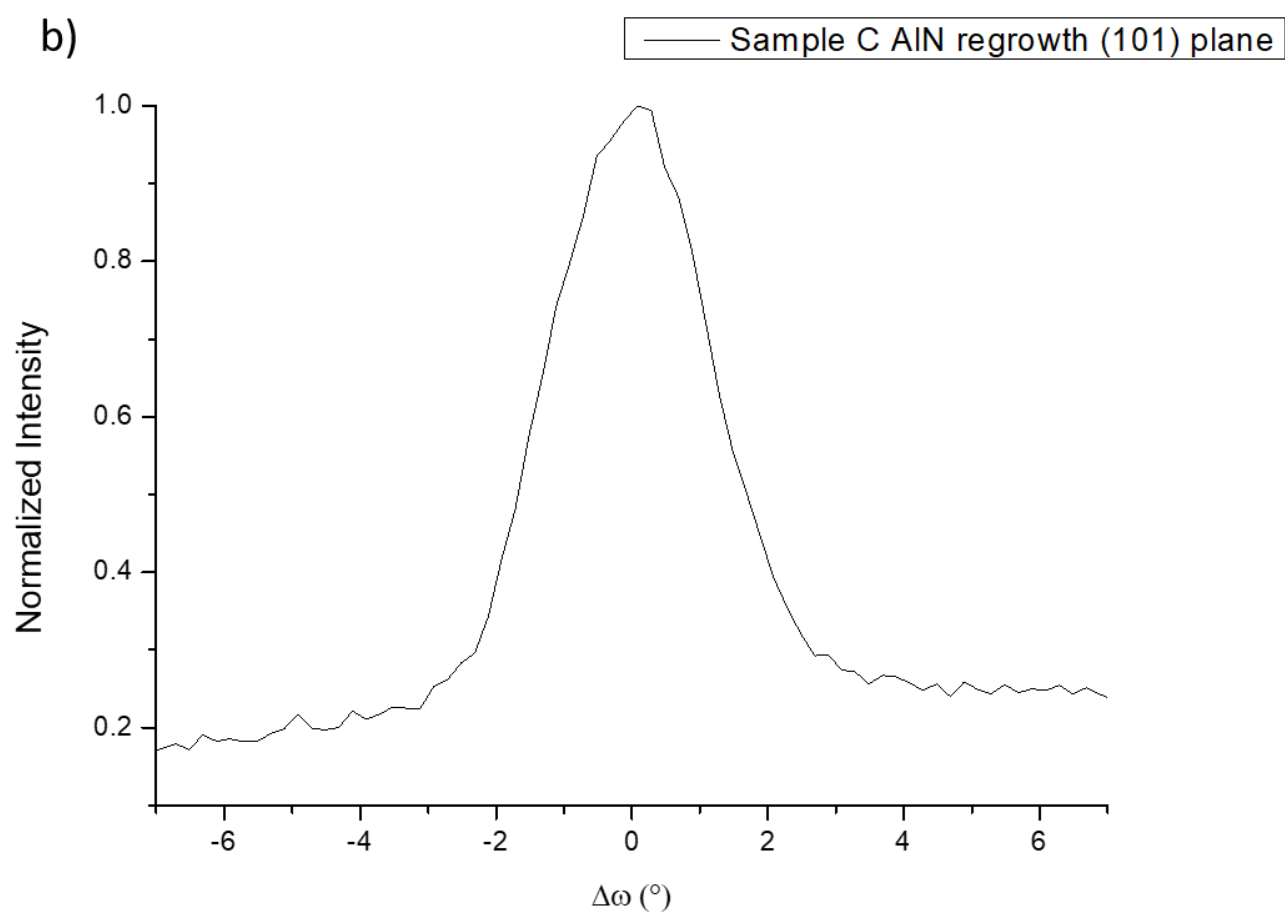


Figure S3. ω -scan of AlN (sample C) after regrowth: (a) for the symmetric plane (0 0 0 2), (b) for the skew symmetric plane (1 0 -1 1).